

ABSTRACT

A method for manufacturing a semiconductor device according to the present disclosure includes steps: of preparing a film-shaped adhesive for adhering a semiconductor element to a member for mounting the semiconductor element; and pressure-bonding the semiconductor element to a surface of the member in a state that the film-shaped adhesive and the semiconductor element are stacked on the surface of the member, and an absolute value of a difference between a value E_1 (mJ/m²) of surface free energy of the film-shaped adhesive and a value E_2 (mJ/m²) of surface free energy of the member is in the range of 6.0 to 10.0.

Fig. 1